EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S63	45	("0106828" | "20050187204" | "5408731")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 08:11
S64	2	("20050187204")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 08:11
S65	1	10/558885	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 08:12
S67	6	("0106828" | "20050187204" | "5408731").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:35
S68	2	("20050187204").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:36
S69	883	silicon near3 microphone	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:38
S70	434	S69 and diaphragm	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:39

S71	90	S70 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 21:39
S72	200119	first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:00
S73	40040	(first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:01
S74	18062	S72 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:01
S75	4075	S74 and (trench via groove hole recess opening via cavity) near3 oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:02
S76	291	S75 and (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:05
S77	50	S76 and (movable diaphragm)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/13 22:06
S78	200243	first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 05:59

S79	18064	S78 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 05:59
S80	5508	S79 and (trench via groove hole recess opening via cavity) near3 etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 05:59
S81	569	S80 and (aperture acoutic near3 hole) with (aperture acoutic near3 hole)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:00
S82	5	S80 and (aperture acoutic near3 hole) with (aperture acoutic near3 hole) same (microphone pressure near3 sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:01
S83	5	S80 and (aperture acoutic near3 hole) same (microphone pressure near3 sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:04
S84	7536	438/22,48-53.ccls. 257/254,419.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:05
S85	1688	S84 and first near3 (wafer substrate) same second near3 (wafer substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:06
S86	499	S84 and (first near3 (wafer substrate) second near3 (wafer substrate)) with oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/04/14 06:07

| S87 | 63 | S86 and (aperture acoutic near3 hole) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/04/14 06:07 |
| S88 | 183 | S86 and (trench via groove hole recess opening via cavity) near3 oxide | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2010/04/14 06:08 |

4/14/2010 7:15:22 AM
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